

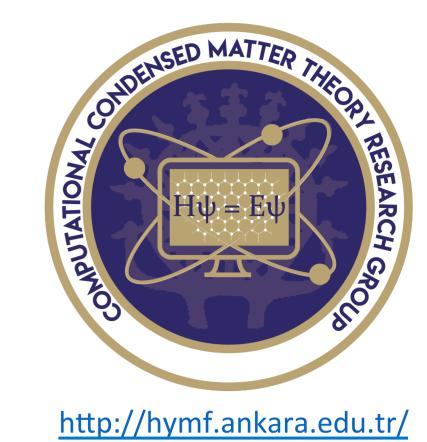




# Boron phosphide based 2D heterostructures

#### **YESIM MOGULKOC<sup>1</sup>**, AYBEY MOGULKOC<sup>2</sup> and MOHSEN MODARRESI<sup>3</sup>

<sup>1</sup>Department of Physics Engineering, Faculty of Engineering, Ankara University, Ankara, Turkey <sup>2</sup>Department of Physics, Faculty of Science, Ankara University, Ankara, Turkey <sup>3</sup>Department of Physics, Ferdowsi University of Mashhad, Mashhad, Iran



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#### MOTIVATION

#### SCOPE

With the down-sizing of devices in the electronics industry, 2D layered materials have become the focus of experimental and theoretical work due

We analyze the variation of the energy band gap, the characteristics of the energy band diagram of the boron based 2D systems which are boron phosphide/blue phosphorus and GaN/boron phosphide

- to their low dimensional interface properties.
- Designing alternative versatile 2D heterostructures improve electronic and optical properties compared with monolayer 2D materials due to the mutual interaction between the layers.
- $\Box$  Boron phosphide has superior carrier mobility (over 10<sup>4</sup> cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>).
- Band gaps are changing according to the layers.

### METHOD

- First-principles calculations are based on density functional theory (DFT) performed by VASP package.
- The exchange-correlation potentials are approximated by the generalized gradient approximation (GGA) with the Perdew– Burke–Ernzerhof (PBE) and hybrid Heyd–Scuseria–Ernzerhof (HSE06) functionals.
- The van der Waals interaction is important for layered hetero- structures which is taken into account by the **DFT-D2** method.

## **Geometrical Structures**

**Monolayer boron phosphide/blue phosphorus heterostructures** 

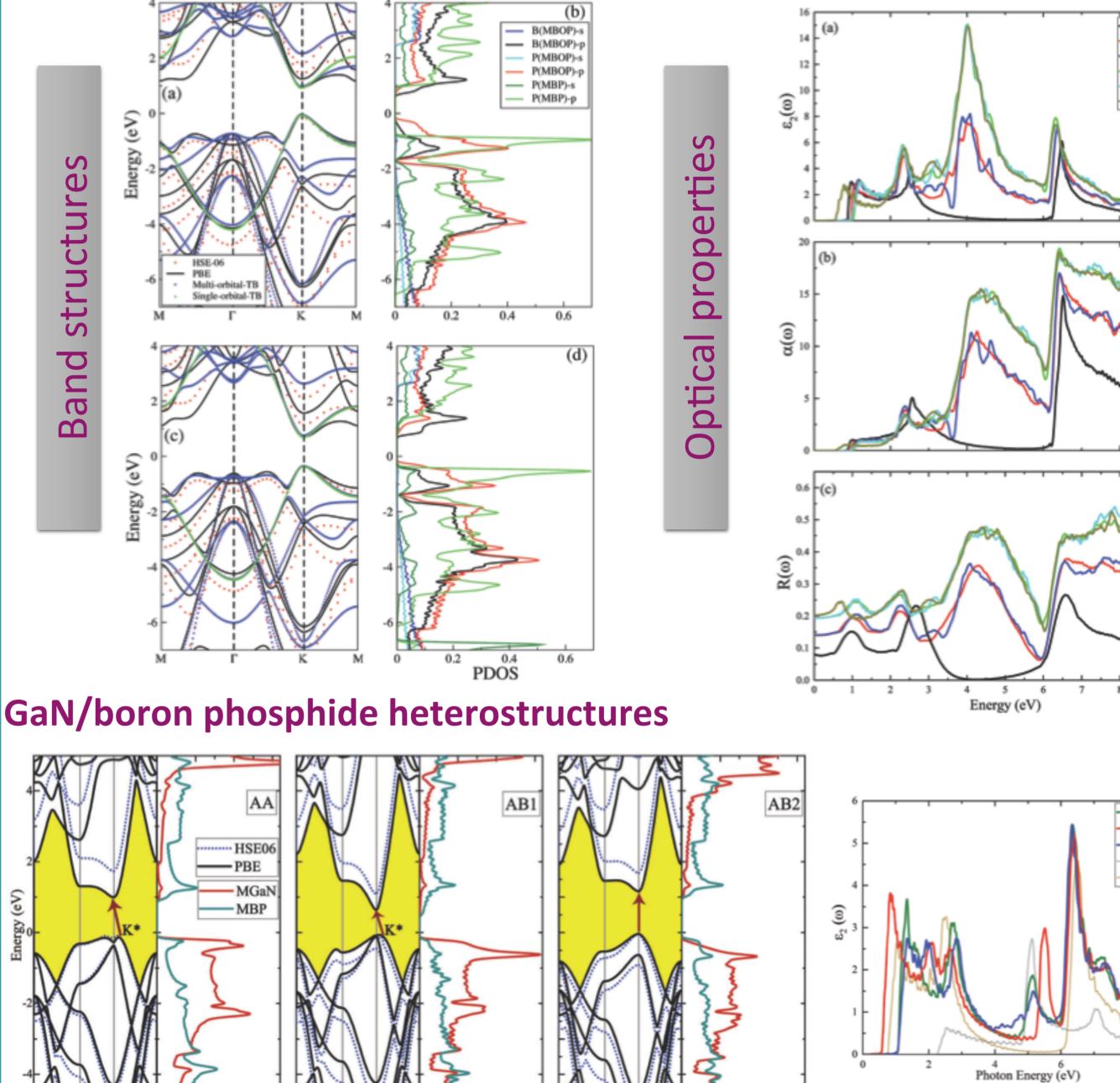


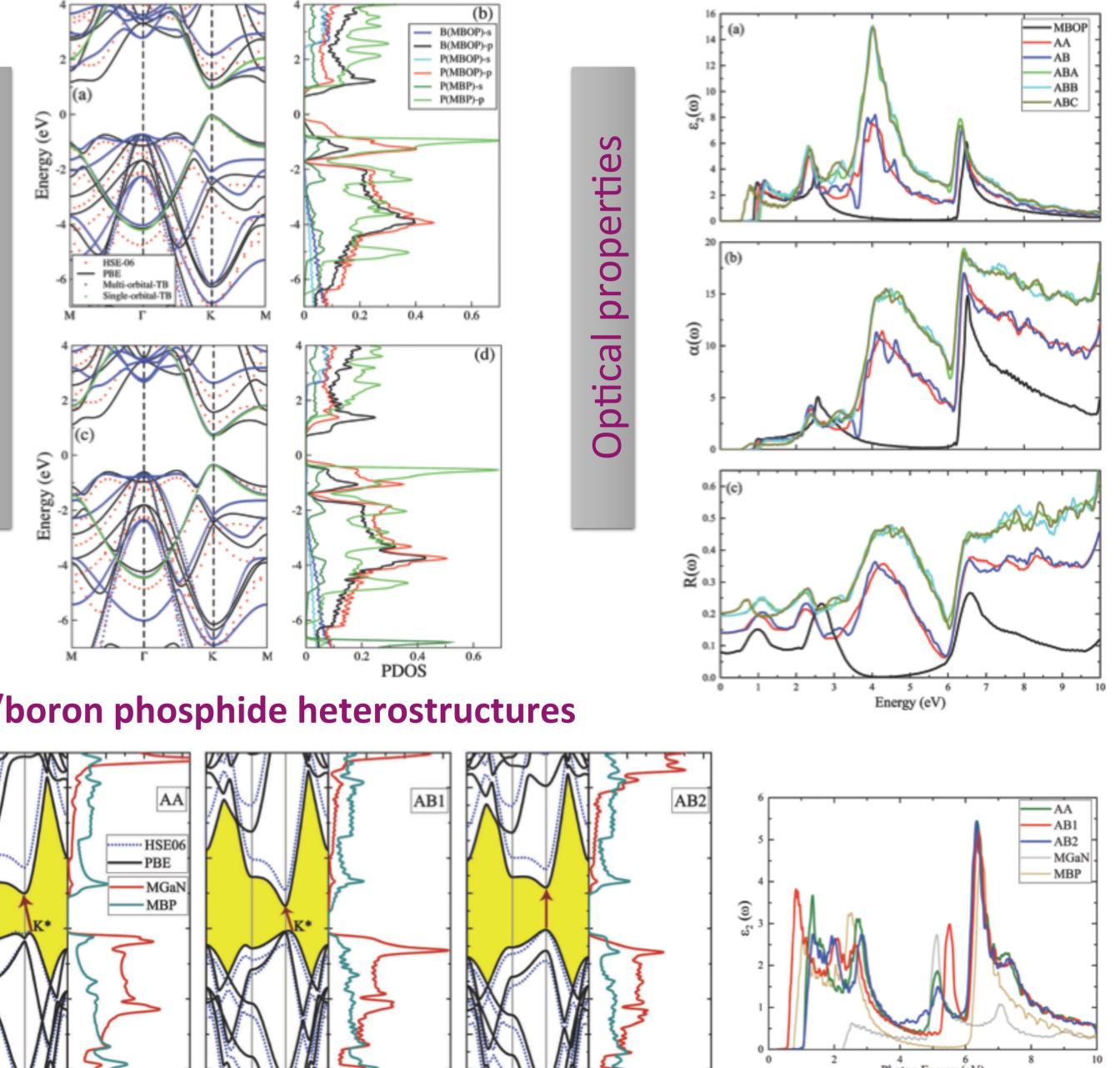
- We examine the optical properties of monolayer boron phosphide and heterostructures as part of DFT calculations.
- We have also analyzed these properties under the external electric field.
- ? Can we recommend boron phosphide based 2D heterostructures for optoelectronic applications?

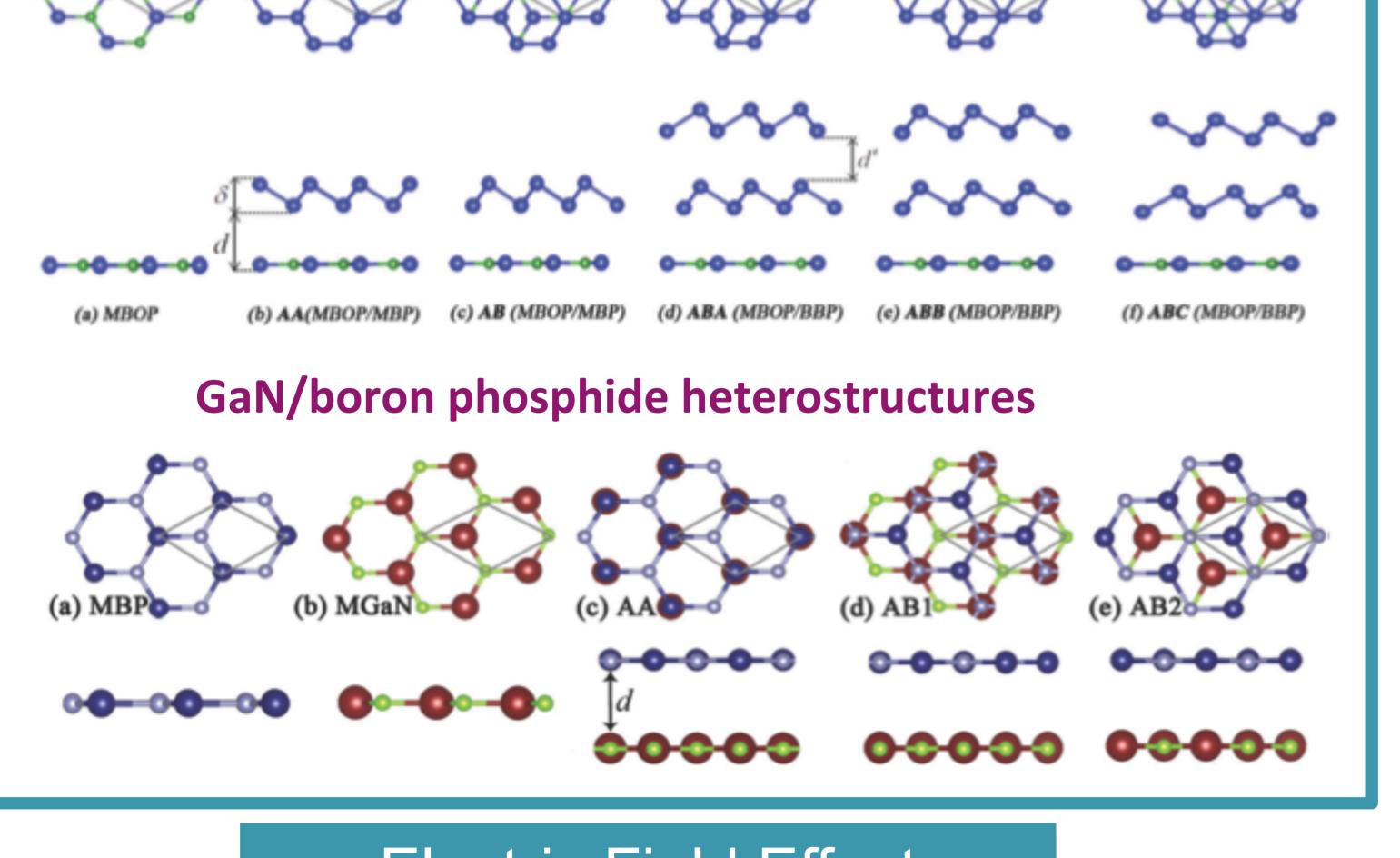


## Electronic & Optical Properties

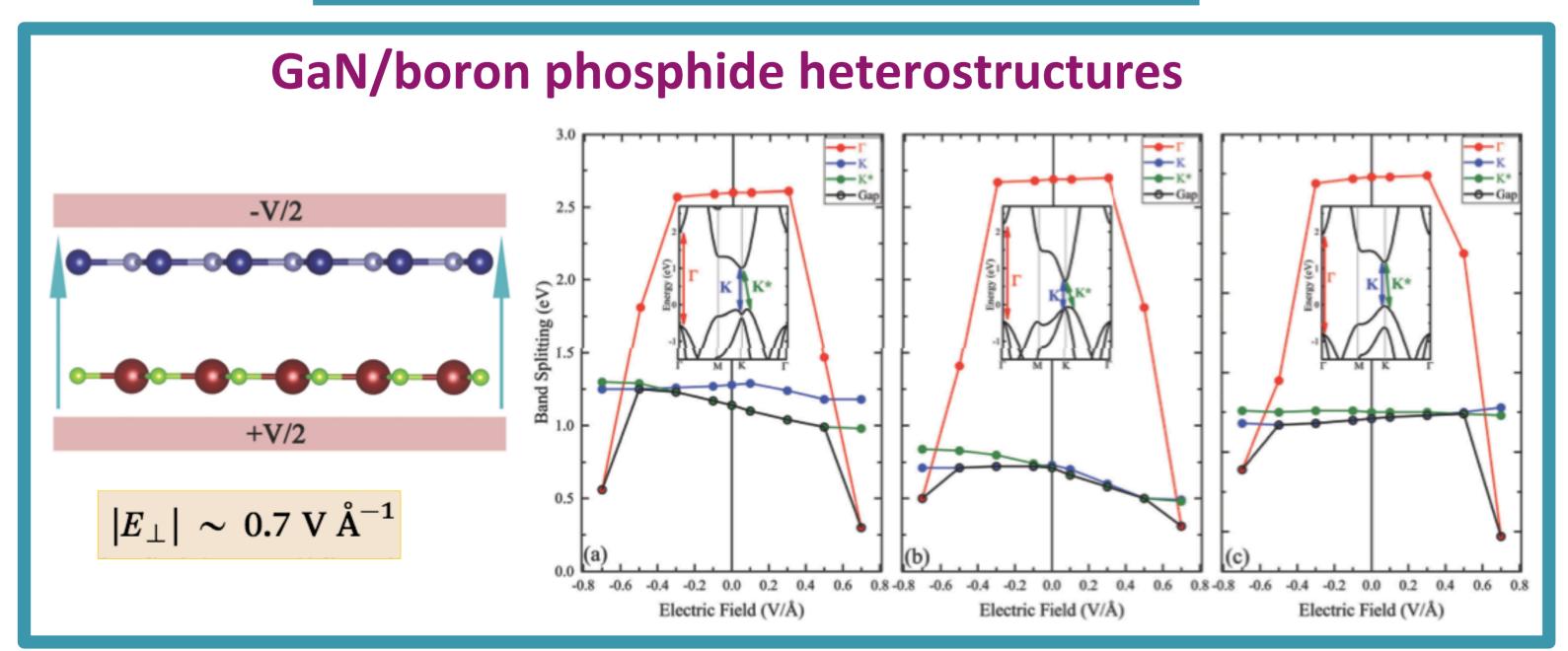
#### **Monolayer boron phosphide/blue phosphorus heterostructures**







### Electric Field Effect



#### CONCLUSIONS

r PDOS (eV/state)

r PDOS (eV/state)

All of the heterostructures that are proposed are found to be stable by considering the phonon spectra.

M K

PDOS (eV/state)

- Pristine MBP has an indirect energy band gap, and heterobilayers of MBOP/ ••• MBP have direct band gaps.
- For the MGaN/MBOP system, while AA and AB1 are found to be indirect band gap semiconductors, AB2 has a direct band gap where the MBP layer dominates the band structure.
- Finally, we examined the optical properties of the heterostructures by considering the frequency dependent imaginary dielectric function.
- It is also seen that the prominent optical absorption of the heterobilayers arises from the UV range, promising for optoelectronic applications based on the UV spectral region.

#### REFERENCES CONTACT PERSON

Yeşim Moğulkoç

mogulkoc@eng.ankara.edu.tr

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